

● General Description

The AGMH035N10A combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

● Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

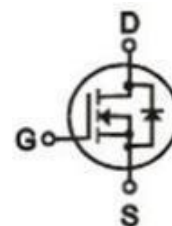
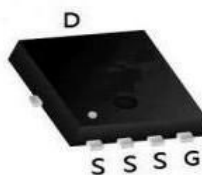
● Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
100V	3.6mΩ	112A

PDFN5*6 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
AGMH035N10A	AGMH035N10A	PDFN5*6	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	100	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	112	A
	Drain Current-Continuous(Tc=100°C)	78	A
IDM (pluse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	400	A
PD	Maximum Power Dissipation(Tc=25°C)	104	w
	Maximum Power Dissipation(Tc=100°C)	42	w
EAS	Avalanche energy (Note 3)	375	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	50	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	1.2	°C/W

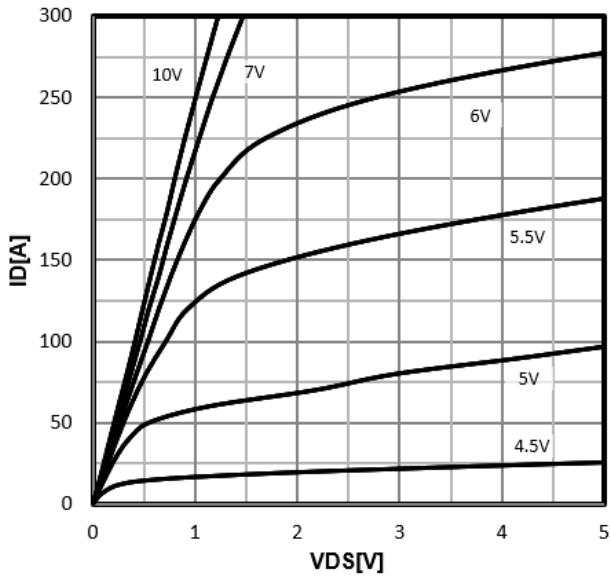
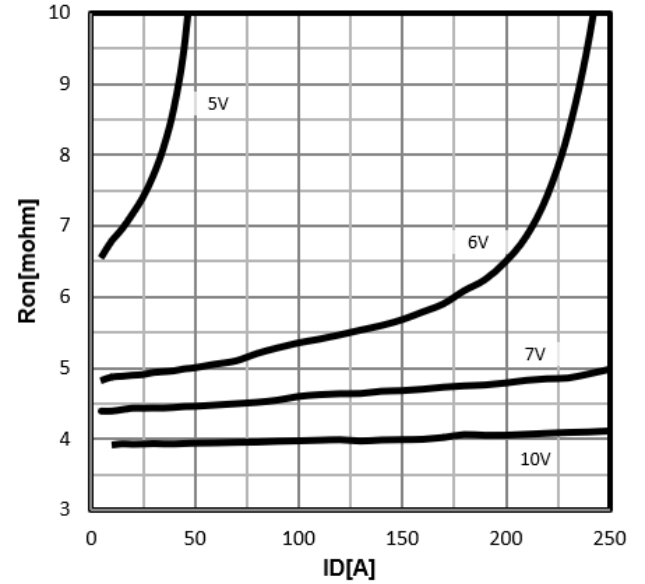
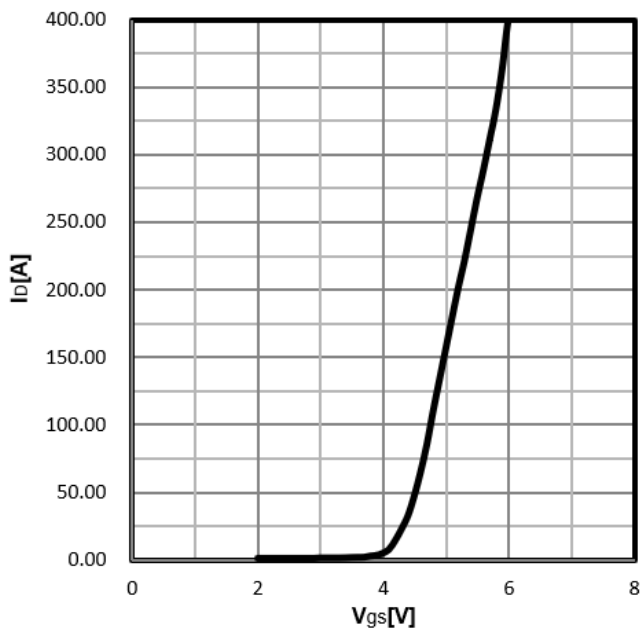
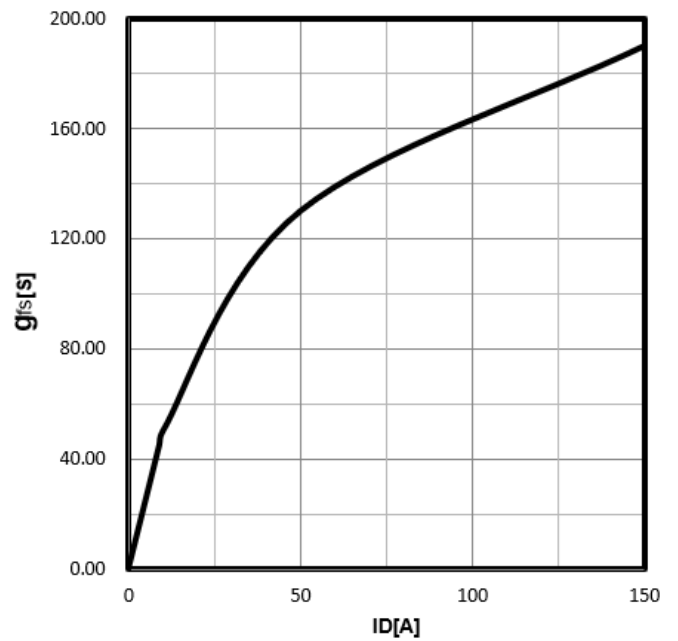
Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	100	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=100V,VGS=0V	--	--	1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	2.5	3.0	3.5	V
gFS	Forward Transconductance	VDS=5V,ID=56A	--	130	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=10V, ID=56A	--	3.6	4.1	mΩ
		VGS=4.5V, ID=50A	--	--	--	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=50V,VGS=0V, F=1MHZ	--	3950	--	pF
Coss	Output Capacitance		--	1200	--	pF
Crss	Reverse Transfer Capacitance		--	27	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	2.1	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=10V,VDS=50V, ID=56A,RGEN=5Ω	--	25	--	nS
tr	Turn-on Rise Time		--	33	--	nS
td(off)	Turn-Off Delay Time		--	95	--	nS
tf	Turn-Off Fall Time		--	75	--	nS
Qg	Total Gate Charge	VGS=10V, VDS=50V, ID=56A	--	67.2	--	nC
Qgs	Gate-Source Charge		--	16.9	--	nC
Qgd	Gate-Drain Charge		--	16.9	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	112	A
VSD	Forward on Voltage	VGS=0V,IS=56A	--	--	1.2	V
trr	Reverse Recovery Time	IF=20A , dI/dt=100A/μs ,	--	82	--	ns
Qrr	Reverse Recovery Charge	TJ=25°C	--	180	--	nc

Notes 1.The maximum current rating is package limited.

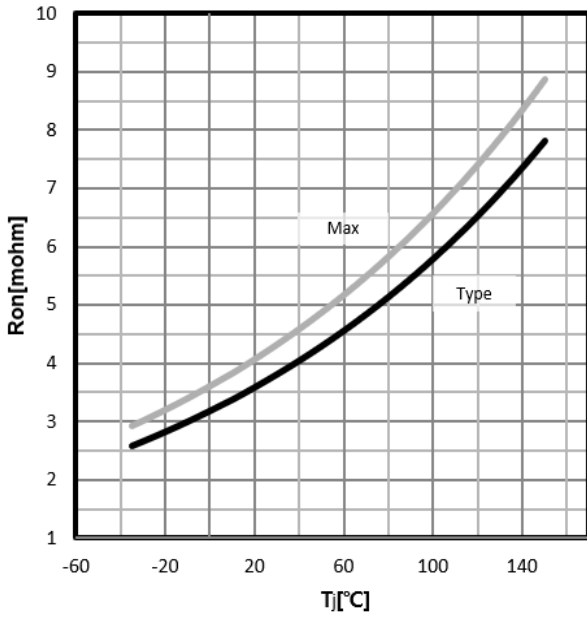
Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

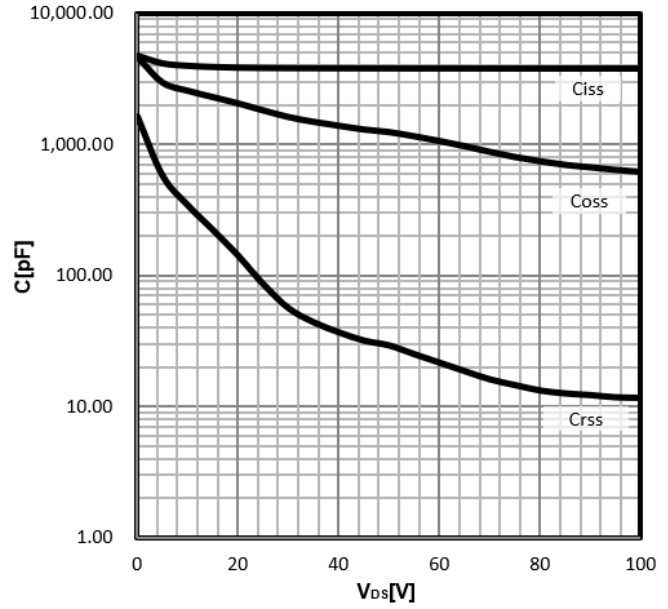
Characteristics Curve:
Typ. output characteristics
 $I_D = f(V_{DS})$

Typ. drain-source on resistance
 $R_{DS(on)} = f(I_D)$

Typ. transfer characteristics
 $I_D = f(V_{GS})$

Typ. forward transconductance
 $g_{fs} = f(I_D)$


Drain-source on-state resistance

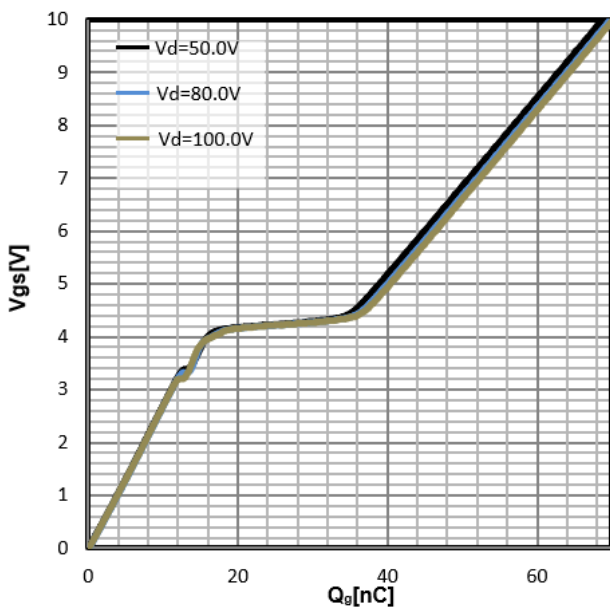
$$R_{DS(on)} = f(T_j); I_D = 56A; V_{GS} = 10V$$


Typ. capacitances

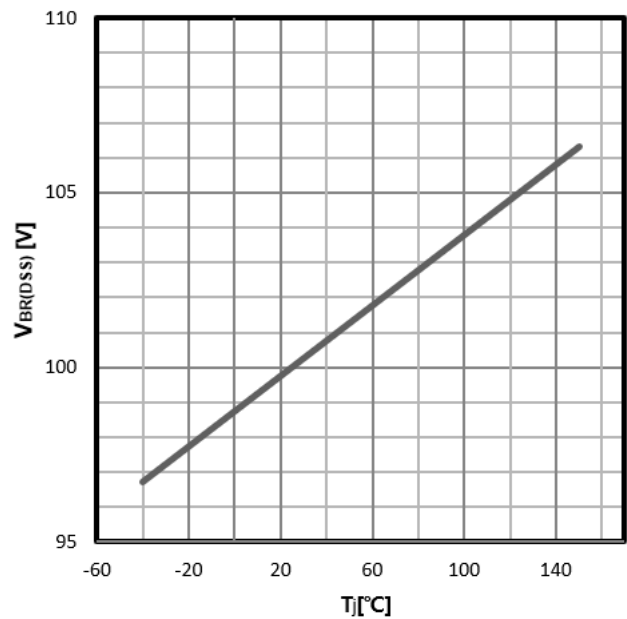
$$C = f(V_{DS}); V_{GS} = 0V; f = 1MHz$$


Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 20A$$

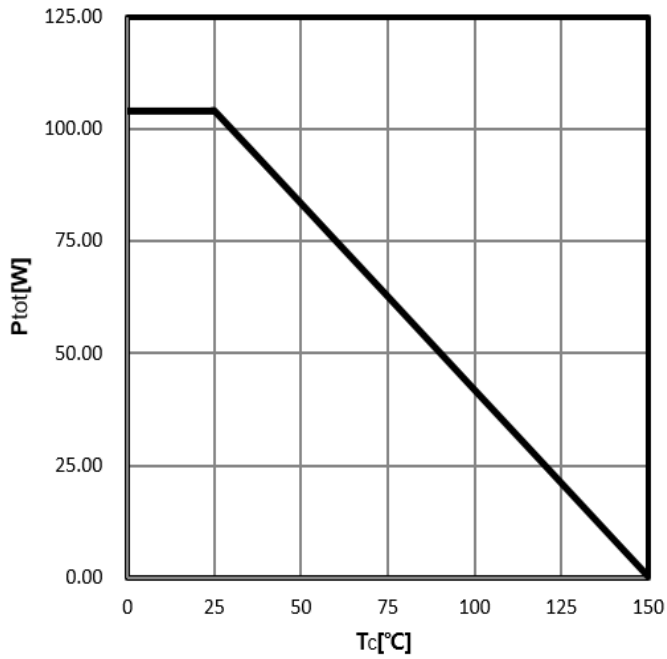

Drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 250\mu A$$

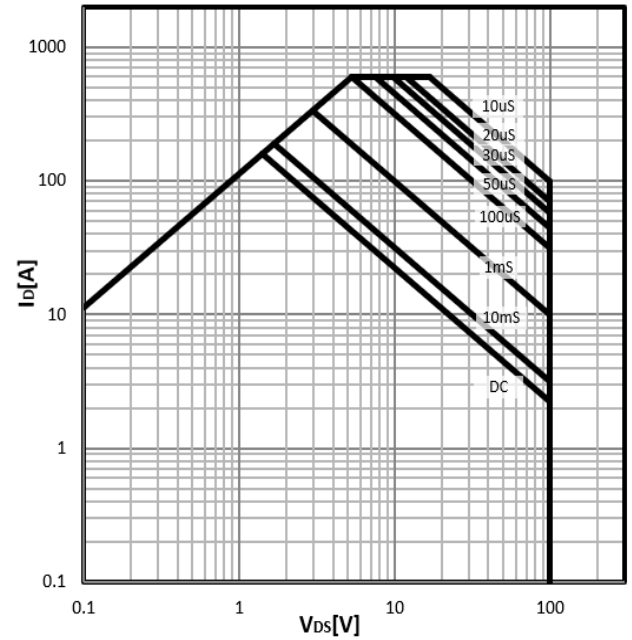


Power Dissipation

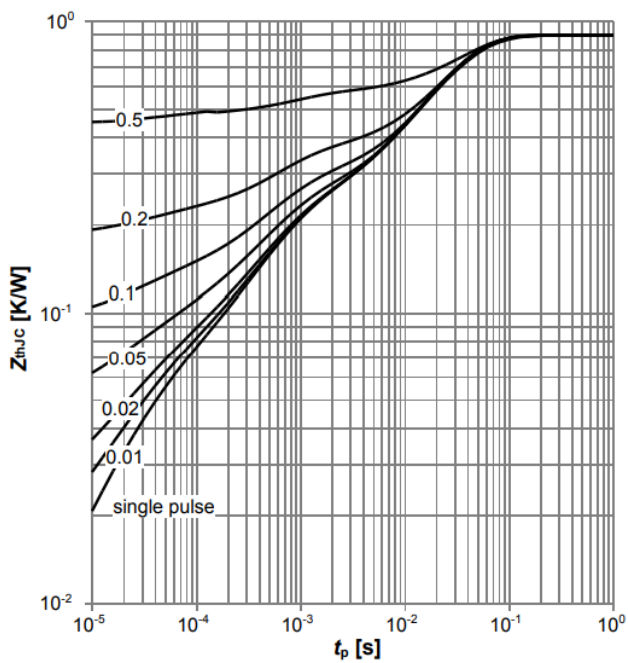
$$P_{tot}=f(T_c)$$

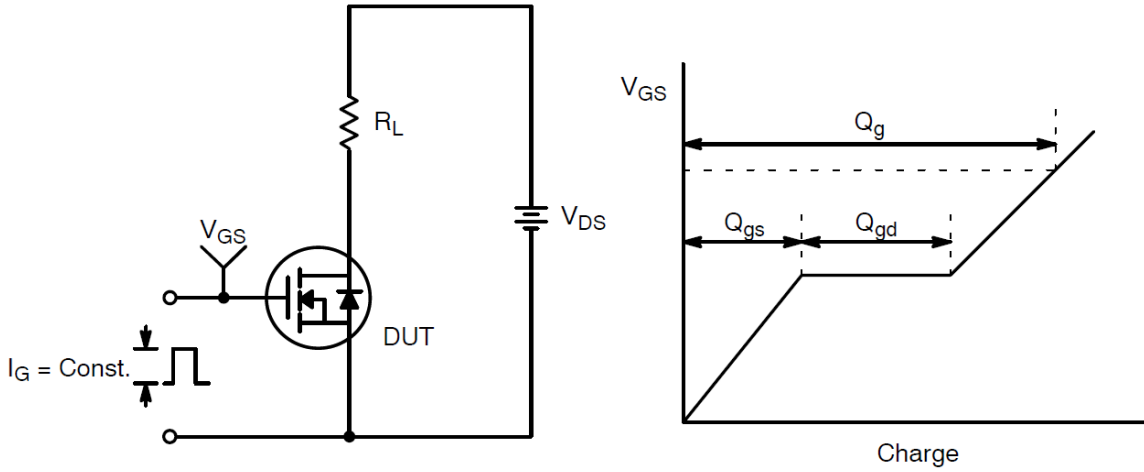
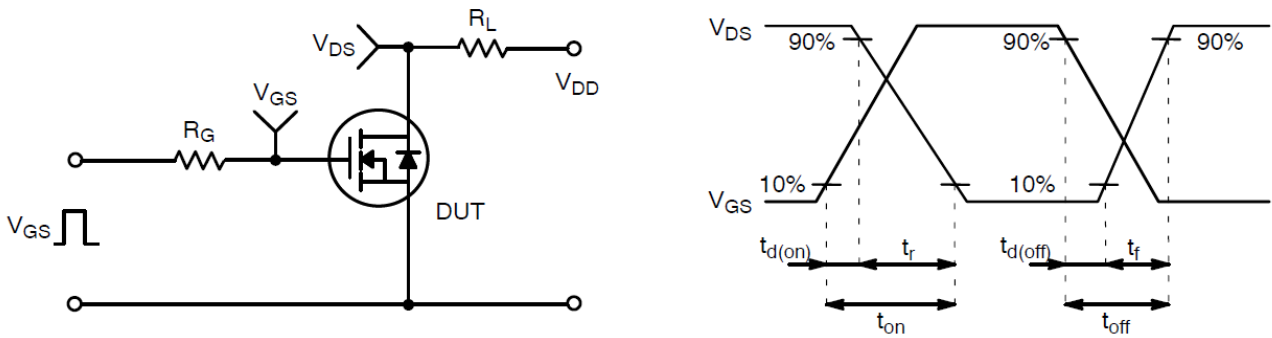
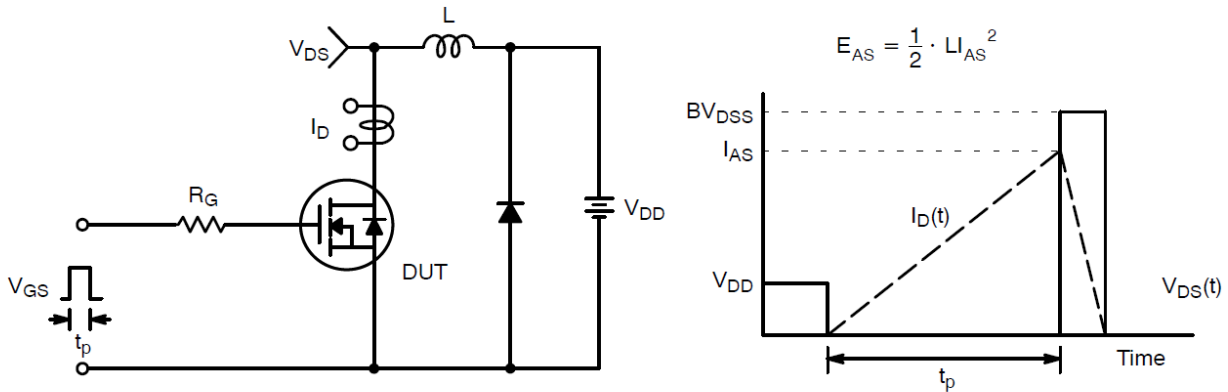

Safe operating area

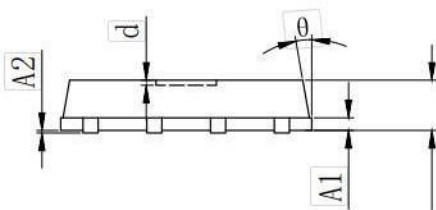
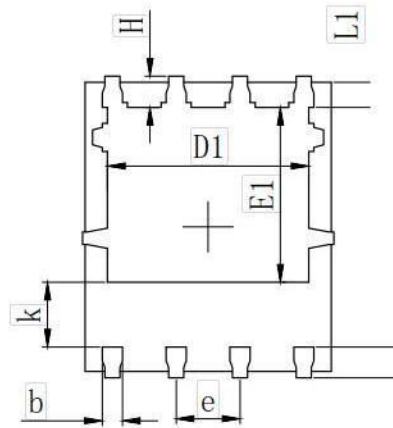
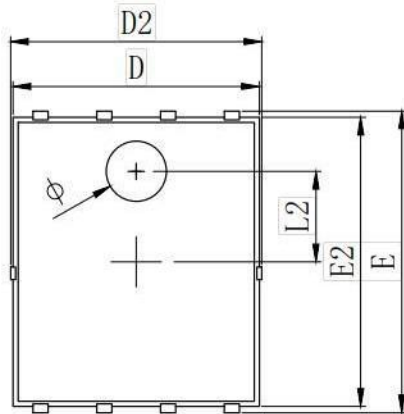
$$I_D=f(V_{DS})$$


Max. transient thermal impedance

$$Z_{thJC}=f(t_p)$$



Test Circuit and Waveform:

Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveforms

Unclamped Inductive Switching Test Circuit & Waveforms

•Dimensions (DFN5×6)


SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	0.900	1.000	1.100
A1	0.254 REF.		
A2	0~0.05		
D	4.824	4.900	4.976
D1	3.910	4.010	4.110
D2	4.924	5.000	5.076
E	5.924	6.000	6.076
E1	3.375	3.475	3.575
E2	5.674	5.750	5.826
b	0.350	0.400	0.450
e	1.270 TYP.		
L	0.534	0.610	0.686
L1	0.424	0.500	0.576
L2	1.800 REF.		
k	1.190	1.290	1.390
H	0.549	0.625	0.701
θ	8°	10°	12°
∅	1.100	1.200	1.300
d			0.100


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